

Special Devices

Silicon controlled switches

TYPE NO.	P _D @ T _A = 25°C	I _A max.	NPN			PNP		V _F max.	I _H @ I _{Ga} min./max.	t _{on} max.	CASE
			BV _{CB0}	h _{FE} @ V _{CE} @ I _C min.	V _{CE(sat)} @ I _C max.	h _{FE} @ I _C min.					
MAS 32	250mW	100mA	70V	50 @ 2V @ 10mA	0.5V @ 10/1mA	0.250 @ 1mA	1.4V	0.1/1mA @ 10mA	250ns	TO-72	
MAS 39	250mW	100mA	50V	30 @ 2V @ 10mA	0.8V @ 10/1mA	0.250 @ 1mA	1.4V	0.1/1mA @ 10mA	250ns	TO-72	
BR 101	250mW	100mA	50V	50 @ 2V @ 10mA	0.6V @ 10/1mA	0.125 @ 1mA	1.4V	0.1/1mA @ 10mA	250ns	TO-72	
BRY 39	250mW	100mA	70V	55 @ 2V @ 10mA	0.5V @ 10/1mA	0.125 @ 1mA	1.4V	0.1/1mA @ 10mA	250ns	TO-72	

Programmable unijunction transistors

TYPE NO.	P _D @ T _A = 25°C	I _A max.	BV _{KAO} min.	BV _{KGO} min.	V _{AK} min.	V _T max.	V _F @ I _F max.	I _P max.	I _V max.	I _{GKS} max.	I _{GAO} max.	CASE
MEU 21	250mW	150mA	40V	5V	40V	0.6V	1.5V @ 50mA	2000nA	50μA	100nA	10nA	TO-106
MEU 22	250mW	150mA	40V	5V	40V	0.6V	1.5V @ 50mA	150nA	25μA	100nA	10nA	TO-106
MTU 21	75mW	150mA	40V	5V	40V	0.6V	1.5V @ 50mA	2000nA	50μA	100nA	10nA	MT-42
MTU 22	75mW	150mA	40V	5V	40V	0.6V	1.5V @ 50mA	150nA	25μA	100nA	10nA	MT-42
PUT 1	250mW	150mA	20V	5V	20V	0.6V	1.5V @ 50mA	1000nA	—	100nA	10nA	TO-106
PUT 2	250mW	150mA	40V	5V	40V	0.6V	1.5V @ 50mA	1000nA	—	100nA	10nA	TO-106
2N 6027	300mW	20mA	40V	5V	40V	1.6V	1.5V @ 50mA	2000nA	70μA	100nA	10nA	TO-92BF
2N 6028	300mW	20mA	40V	5V	40V	0.6V	1.5V @ 50mA	1500nA	25μA	100nA	10nA	TO-92BF

Silicon phototransistors

TYPE NO.	P _D @ T _A = 25°C	I _C max.	BV _{CB0} min.	LV _{CEO} min.	I _L @ V _{CE} @ H min.	I _D @ V _{CE} max.	t _r max.	t _f max.	CASE
MAL 100	200mW	50mA	50V	30V	0.20mA @ 5V @ 20Wm ⁻²	100nA @ 5V	4.0μs	5.0μs	PD-37
MEL 31	200mW	—	40V	30V	0.01mA @ 5V @ 20Wm ⁻²	50nA @ 5V	—	—	TO-106
MEL 32	200mW	—	60V	40V	0.03mA @ 5V @ 20Wm ⁻²	50nA @ 5V	—	—	TO-106
MEL 100	200mW	50mA	50V	30V	0.20mA @ 5V @ 20Wm ⁻²	100nA @ 5V	4.0μs	5.0μs	TO-106
MEPT 100	200mW	25mA	50V	30V	0.20mA @ 5V @ 50Wm ⁻²	100nA @ 5V	2.8μs	2.8μs	TO-106
MEPT 100A	200mW	25mA	50V	30V	1.00mA @ 5V @ 50Wm ⁻²	100nA @ 5V	2.8μs	2.8μs	TO-106
MEPT 100B	200mW	25mA	50V	30V	1.30mA @ 5V @ 50Wm ⁻²	100nA @ 5V	2.8μs	2.8μs	TO-106

Photo detectors

TYPE NO.	P _D @ T _A = 25°C	I _C max.	BV _{CB0} min.	LV _{CEO} min.	I _L @ V _{CE} @ H min.	I _D @ V. max.	t _r max.	t _f max.	t _d max.	t _s max.	CASE
MEL 11	200mW	150mA	40V	30V	0.5mA @ 5V @ 20Wm ⁻²	100nA @ 5V	100μs	75μs	60μs	50μs	TO-106
MEL 12	200mW	150mA	60V	40V	1.0mA @ 5V @ 20Wm ⁻²	100nA @ 5V	100μs	75μs	60μs	50μs	TO-106